transphorm

TP65H050BS

650V GaN FET in TO-263 (source tab)

Preliminary Datasheet

Description

The TP65H050BS 650V, 50mΩ Gallium Nitride (GaN) FET is a normally-off device. It combines state-of-the-art high voltage GaN HEMT and low voltage silicon MOSFET technologies—offering superior reliability and performance.

Transphorm GaN offers improved efficiency over silicon, through lower gate charge, lower crossover loss, and smaller reverse recovery charge.

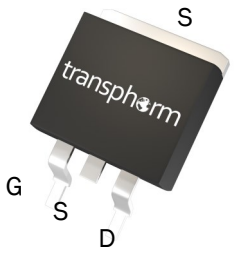
Related Literature

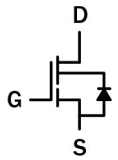
- AN0009: Recommended External Circuitry for GaN FETs
- AN0003: Printed Circuit Board Layout and Probing
- AN0010: Paralleling GaN FETs

Ordering Information

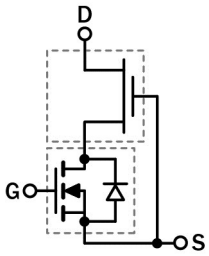
Part Number	Package	Package Configuration
TP65H050BS	TO-263	Common Source

TP65H050BS
TO-263
(top view)





Cascode Schematic Symbol



Cascode Device Structure

Features

- JEDEC qualified GaN technology
- Dynamic $R_{DS(on)eff}$ production tested
- Robust design, defined by
  - Intrinsic lifetime tests
  - Wide gate safety margin
  - Transient over-voltage capability
- Very low Q_{RR}
- Reduced crossover loss
- RoHS compliant and Halogen-free packaging

Benefits

- Enables AC-DC bridgeless totem-pole PFC designs
  - Increased power density
  - Reduced system size and weight
  - Overall lower system cost
- Achieves increased efficiency in both hard- and soft-switched circuits
- Easy to drive with commonly-used gate drivers
- GSD pin layout improves high speed design

Applications

- Datacom
- Broad industrial
- PV inverter
- Servo motor

Key Specifications	
V_{DSS} (V)	650
$V_{(TR)DSS}$ (V)	800
$R_{DS(on)eff}$ (mΩ) max*	60
Q_{RR} (nC) typ	125
Q_G (nC) typ	16

* Dynamic on-resistance; see Figures 14 and 15

Absolute Maximum Ratings (T_C=25°C unless otherwise stated.)

Symbol	Parameter		Limit Value	Unit
V_{DSS}	Drain to source voltage (T_J = -55°C to 150°C)		650	V
$V_{(TR)DSS}$	Transient drain to source voltage [a]		800	
V_{GSS}	Gate to source voltage		±20	
P_D	Maximum power dissipation @T_C=25°C		119	W
I_D	Continuous drain current @T_C=25°C [b]		36	A
	Continuous drain current @T_C=100°C [b]		25	A
I_{DM}	Pulsed drain current (pulse width: 10µs)		150	A
$(di/dt)_{RDMC}$	Reverse diode di/dt, repetitive [c]		1600	A/µs
$(di/dt)_{RDMT}$	Reverse diode di/dt, transient [d]		3000	A/µs
T_C	Operating temperature	Case	-55 to +150	°C
T_J		Junction	-55 to +150	°C
T_S	Storage temperature		-55 to +150	°C
T_{SOLD}	Soldering peak temperature [e]		260	°C

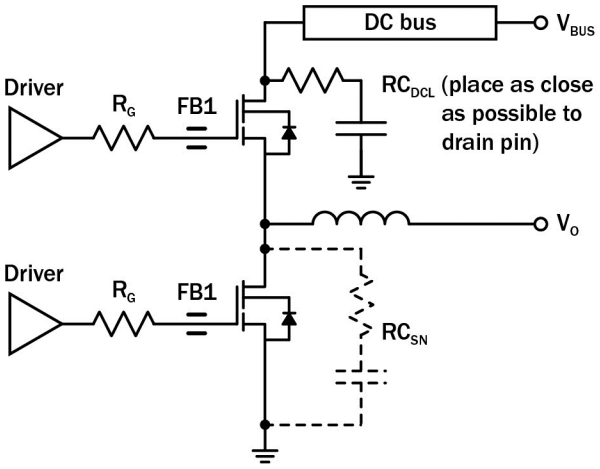
Notes:
a. In off-state, spike duty cycle D<0.01, spike duration <1µs
b. For increased stability at high current operation, see Circuit Implementation on page 3
c. Continuous switching operation
d. ≤300 pulses per second for a total duration ≤20 minutes
e. For 10 sec., 1.6mm from the case

Thermal Resistance

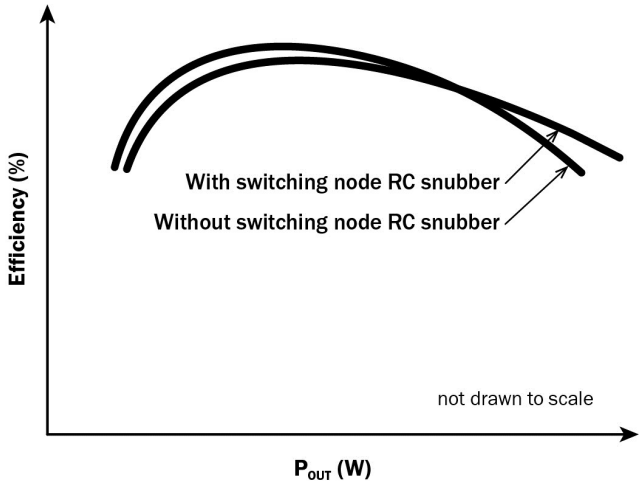
Symbol	Parameter	Max	Unit
$R_{\Theta JC}$	Junction-to-case	1.05	°C/W
$R_{\Theta JA}$	Junction-to-ambient [a]	62	°C/W

Notes:
a. Device on PCB, minimal footprint

Circuit Implementation



Simplified Half-bridge Schematic



Efficiency vs Output Power

Recommended gate drive: (0V, 12V) with $R_{G(tot)}$ = 45Ω, where $R_{G(tot)} = R_G + R_{DRIVER}$

Gate Ferrite Bead (FB1)	Required DC Link RC Snubber (RC_{DCL}) [a]	Recommended Switching Node RC Snubber (RC_{SN}) [b, c]
240Ω @ 100 MHz	[10nF + 8Ω] x 2	100pF + 10Ω

Notes:
a. RC_{DCL} should be placed as close as possible to the drain pin
b. A switching node RC snubber (C, R) is recommended for high switching currents (>70% of I_{RDMC1} or I_{RDMC2}; see page 5 for I_{RDMC1} and I_{RDMC2})
c. I_{RDM} values can be increased by increasing R_G and C_{SN}

Electrical Parameters (T_J=25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
$V_{(BL)DSS}$	Drain-source voltage	650	—	—	V	V_{GS}=0V
$V_{GS(th)}$	Gate threshold voltage	3.3	4	4.8	V	V_{DS}=V_{GS}, I_D=0.7mA
$R_{DS(on)eff}$	Drain-source on-resistance [a]	—	50	60	mΩ	V_{GS}=10V, I_D=22A
		—	103	—		V_{GS}=10V, I_D=22A, T_J=150°C
I_{DSS}	Drain-to-source leakage current	—	2.5	25	μA	V_{DS}=650V, V_{GS}=0V
		—	10	—		V_{DS}=650V, V_{GS}=0V, T_J=150°C
I_{GSS}	Gate-to-source forward leakage current	—	—	100	nA	V_{GS}=20V
		—	—	-100		V_{GS}=-20V
C_{ISS}	Input capacitance	—	1000	—	pF	V_{GS}=0V, V_{DS}=400V, *f*=1MHz
C_{OSS}	Output capacitance	—	130	—		
C_{RSS}	Reverse transfer capacitance	—	8	—		
$C_{O(er)}$	Output capacitance, energy related [b]	—	190	—	pF	V_{GS}=0V, V_{DS}=0V to 400V
$C_{O(tr)}$	Output capacitance, time related [c]	—	310	—		
Q_G	Total gate charge	—	16	24	nC	V_{DS}=400V, V_{GS}=0V to 10V, I_D=22A
Q_{GS}	Gate-source charge	—	6	—		
Q_{GD}	Gate-drain charge	—	5	—		
Q_{OSS}	Output charge	—	124	—	nC	V_{GS}=0V, V_{DS}=0V to 400V
$t_{D(on)}$	Turn-on delay	—	51	—	ns	V_{DS}=400V, V_{GS}=0V to 10V, I_D=22A R_G = 40Ω
t_R	Rise time	—	11	—		
$t_{D(off)}$	Turn-off delay	—	86	—		
t_F	Fall time	—	11	—		

Notes:
a. Dynamic on-resistance; see Figures 14 and 15 for test circuit and conditions
b. Equivalent capacitance to give same stored energy as V_{DS} rises from 0V to 400V
c. Equivalent capacitance to give same charging time as V_{DS} rises from 0V to 400V

Electrical Parameters (T_J=25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Reverse Device Characteristics						
I_S	Reverse current	—	—	22	A	V_{GS}=0V, T_C=100°C, ≤20% duty cycle
V_{SD}	Reverse voltage [a]	—	1,8	2.3	V	V_{GS}=0V, I_S=22A
		—	1.3	1.7		V_{GS}=0V, I_S=11A
t_{RR}	Reverse recovery time	—	54	—	ns	I_S=22A, V_{DD}=400V di/dt=1000A/us
Q_{RR}	Reverse recovery charge	—	125	—	nC	
$(di/dt)_{RDMC}$	Reverse diode di/dt, repetitive [b]	—	—	1600	A/µs	
I_{RDMC1}	Reverse diode switching current, repetitive (dc) [c, e]	—	—	24	A	Circuit implementation and parameters on page 3
I_{RDMC2}	Reverse diode switching current, repetitive (ac) [c, e]	—	—	28	A	Circuit implementation and parameters on page 3
$(di/dt)_{RDMT}$	Reverse diode di/dt, transient [d]	—	—	3000	A/µs	
I_{RDMT}	Reverse diode switching current, transient [d,e]	—	—	36	A	Circuit implementation and parameters on page 3

Notes:
a. Includes dynamic $R_{DS(on)}$ effect
b. Continuous switching operation
c. Definitions: dc = dc-to-dc converter topologies; ac = inverter and PFC topologies, 50-60Hz line frequency
d. ≤300 pulses per second for a total duration ≤20 minutes
e. I_{RDM} values can be increased by increasing R_G and C_{SN} on page 3

Typical Characteristics (T_C=25 °C unless otherwise stated)

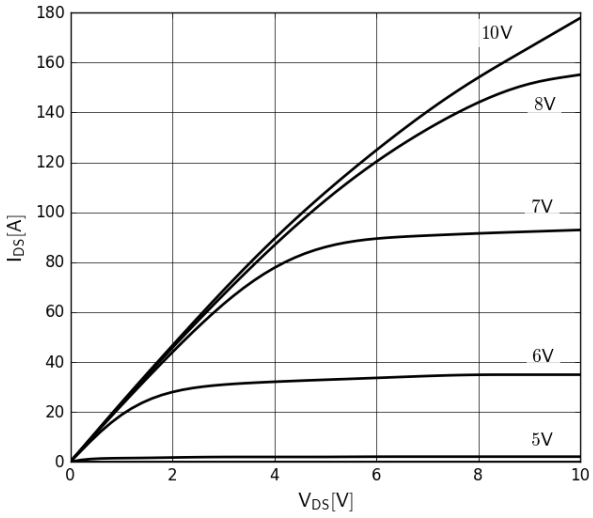


Figure 1. Typical Output Characteristics T_J=25 °C
Parameter: V_{GS}

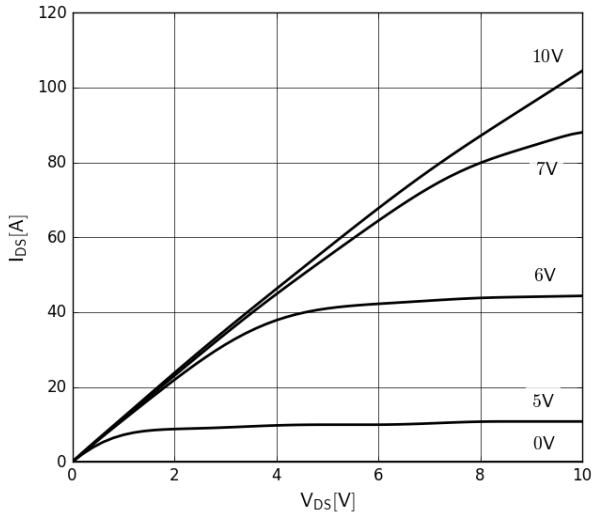


Figure 2. Typical Output Characteristics T_J=150 °C
Parameter: V_{GS}

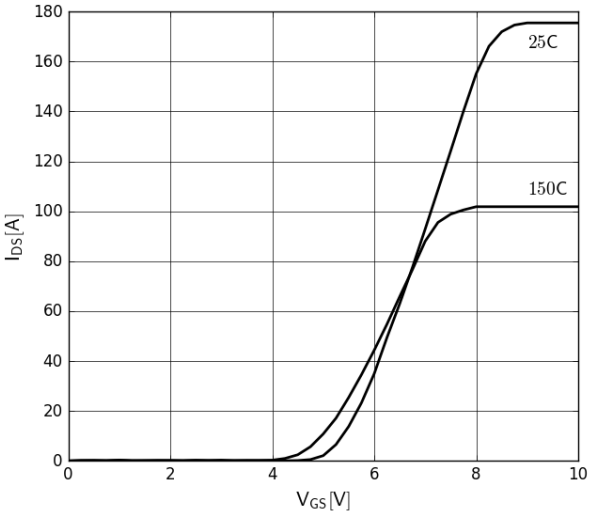


Figure 3. Typical Transfer Characteristics
V_{DS}=10V, parameter: T_J

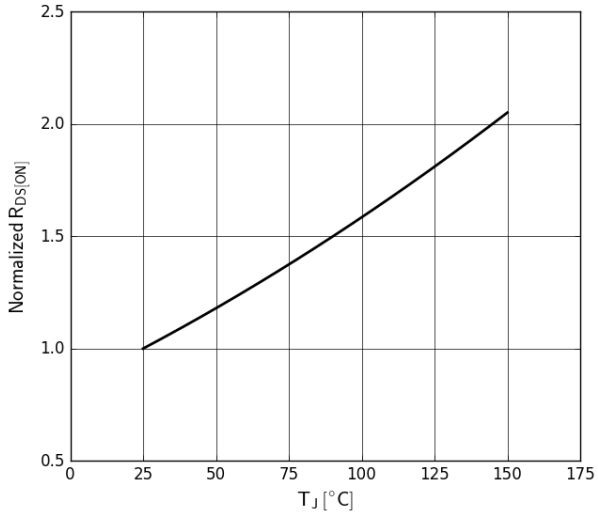


Figure 4. Normalized On-resistance
I_D=22A, V_{GS}=10V

Typical Characteristics (T_C=25 °C unless otherwise stated)

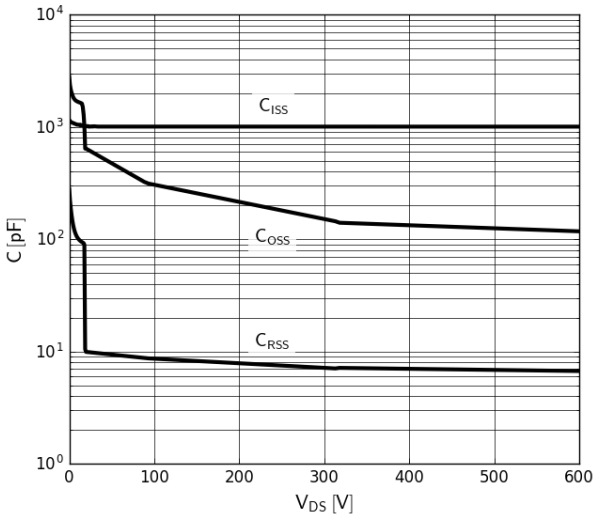


Figure 5. Typical Capacitance
V_{GS}=0V, f=1MHz

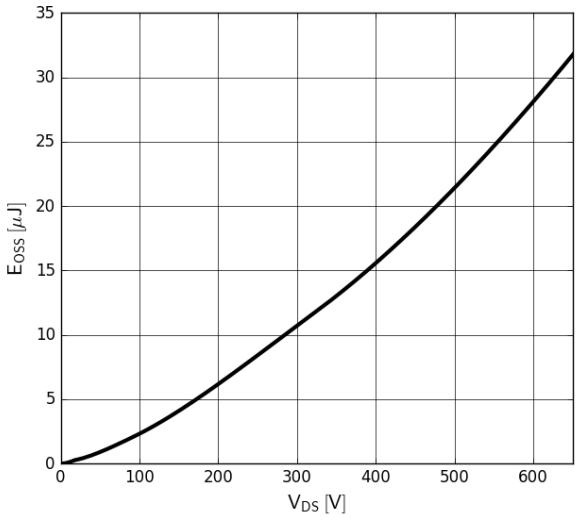


Figure 6. Typical C_{oss} Stored Energy

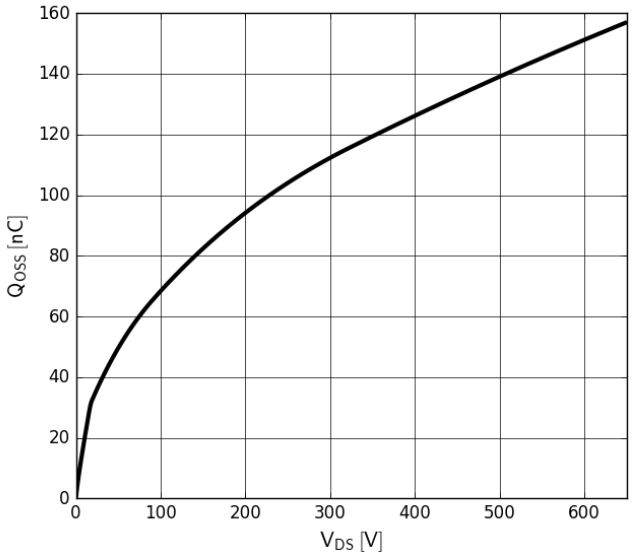


Figure 7. Typical Q_{oss}

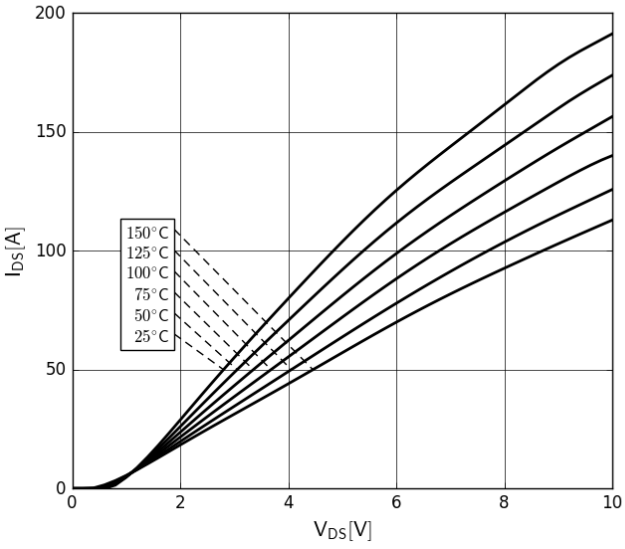


Figure 8. Forward Characteristics of Rev. Diode
I_S=f(V_{SD}), parameter: T_J

Typical Characteristics (T_C=25 °C unless otherwise stated)

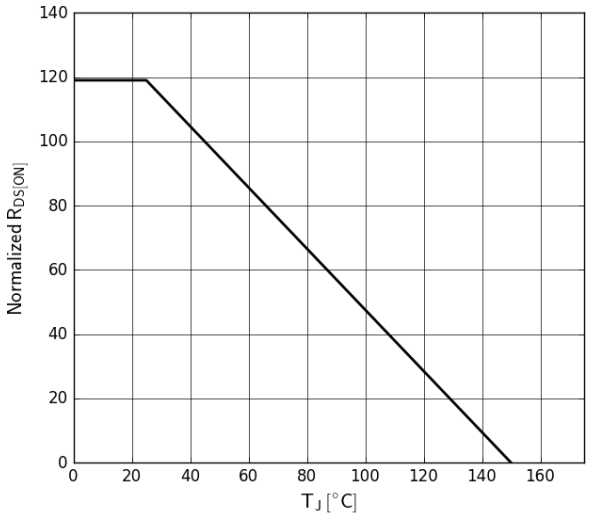


Figure 9. Power Dissipation

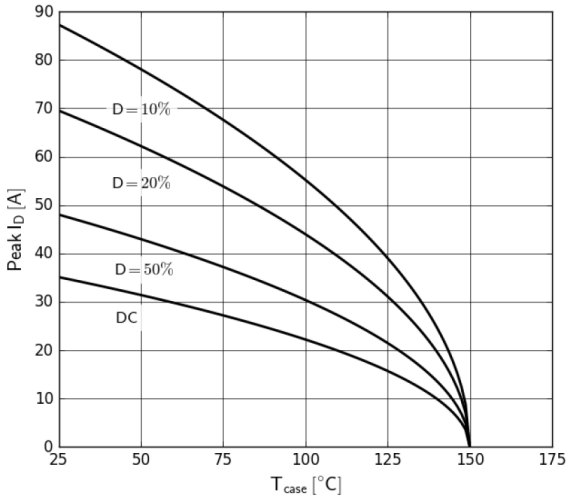


Figure 10. Current Derating
Pulse width ≤ 10µs, V_{GS} ≥ 10V

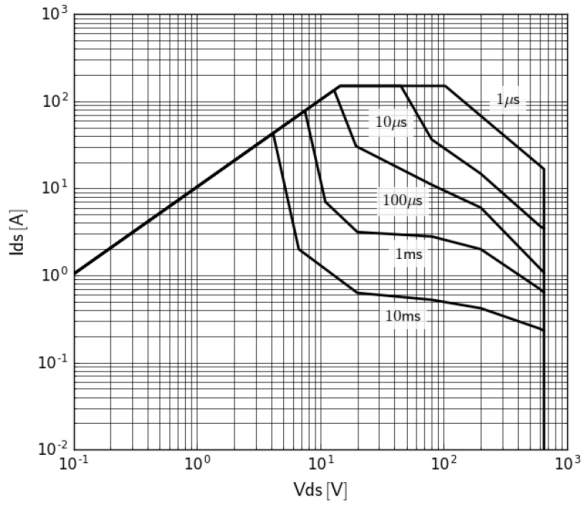


Figure 11. Safe Operating Area T_C=25 °C

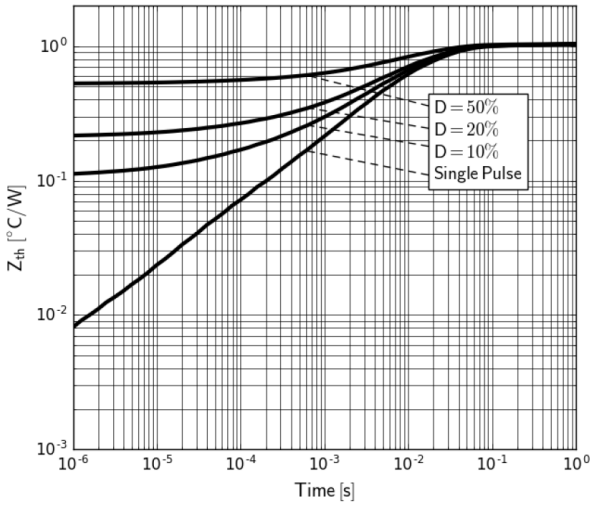


Figure 12. Transient Thermal Resistance

Test Circuits and Waveforms

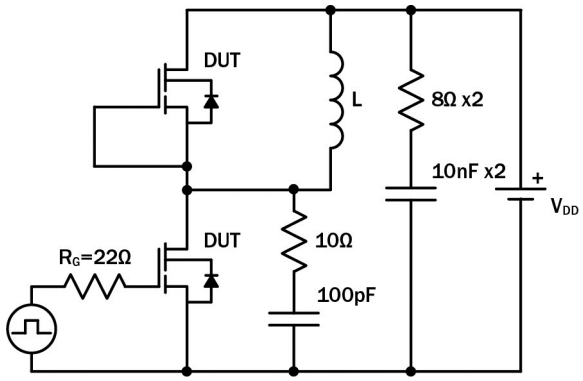


Figure 10. Switching Time Test Circuit
(see circuit implementation on page 3
for methods to ensure clean switching)

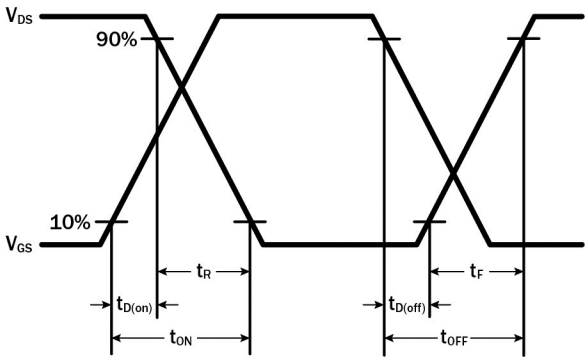


Figure 11. Switching Time Waveform

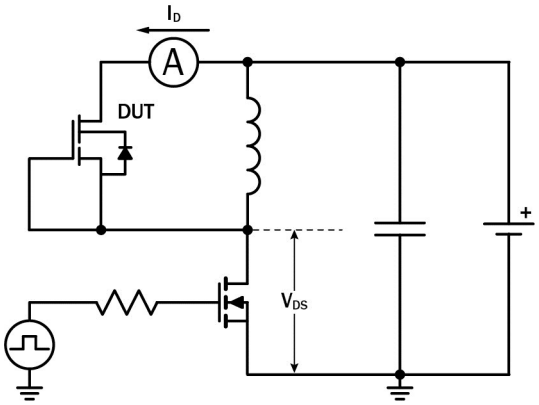


Figure 12. Diode Characteristics Test Circuit

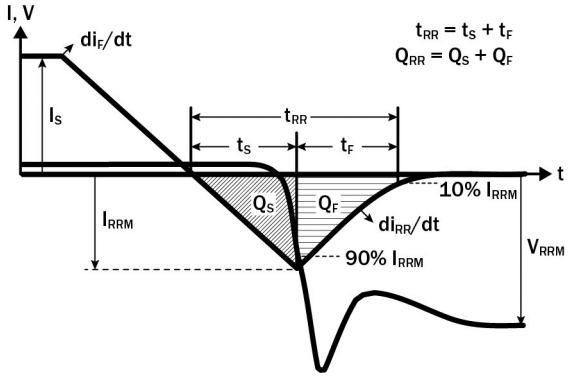


Figure 13. Diode Recovery Waveform

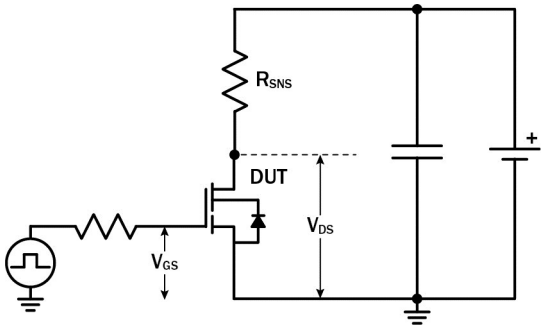


Figure 14. Dynamic $R_{DS(on)eff}$ Test Circuit

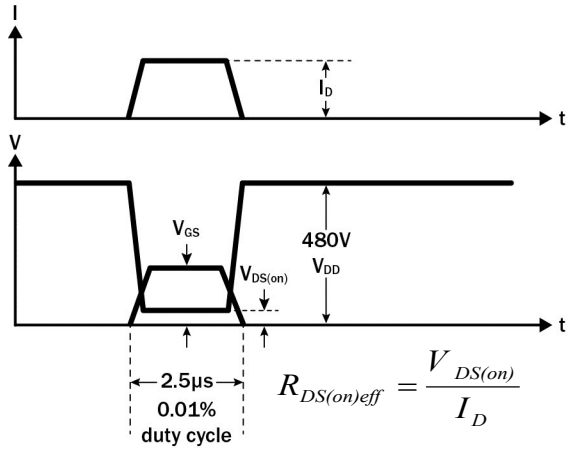


Figure 15. Dynamic $R_{DS(on)eff}$ Waveform

Design Considerations

The fast switching of GaN devices reduces current-voltage crossover losses and enables high frequency operation while simultaneously achieving high efficiency. However, taking full advantage of the fast switching characteristics of GaN switches requires adherence to specific PCB layout guidelines and probing techniques.

Before evaluating Transphorm GaN devices, see application note Printed Circuit Board Layout and Probing for GaN Power Switches. The table below provides some practical rules that should be followed during the evaluation.

When Evaluating Transphorm GaN Devices:

DO	DO NOT
Minimize circuit inductance by keeping traces short, both in the drive and power loop	Twist the pins of TO-220 or TO-247 to accommodate GDS board layout
Minimize lead length of TO-220 and TO-247 package when mounting to the PCB	Use long traces in drive circuit, long lead length of the devices
Use shortest sense loop for probing; attach the probe and its ground connection directly to the test points	Use differential mode probe or probe ground clip with long wire
See AN0003: Printed Circuit Board Layout and Probing	

GaN Design Resources

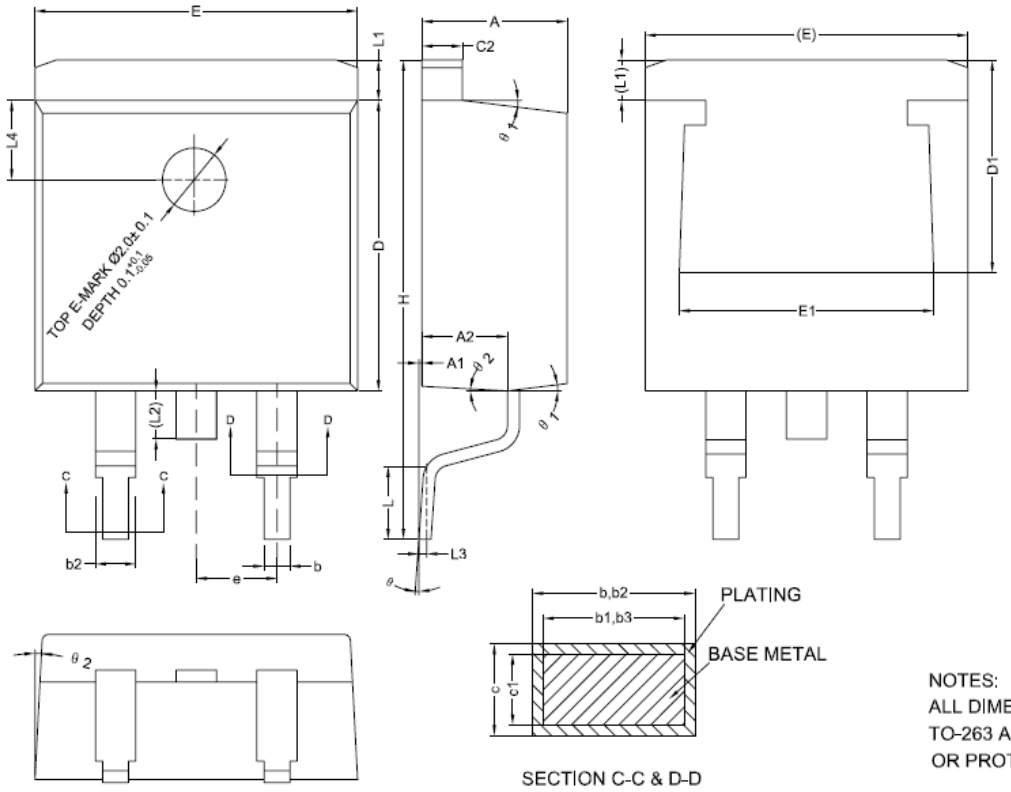
The complete technical library of GaN design tools can be found at transphormusa.com/design:

- Evaluation kits
- Application notes
- Design guides
- Simulation models
- Technical papers and presentations

Mechanical

3 Lead TO-263 (BS) Package

Pin 1: Gate; Pin 2: Source; Pin 3: Drain, Tab: Source



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.57	4.70
A1	0	0.10	0,25
A2	2,59	2.69	2,79
b	0,77	-	0,90
b1	0,76	0.81	0,86
b2	1,23	-	1,36
b3	1,22	1.27	1,32
c	0.34	-	0.47
c1	0,33	0.38	0,43
c2	1,22	-	1,32
D	9,05	9,15	9,25
D1	6,60	-	–
E	10.06	10,16	10.26
E1	7,80	-	8,20
e		2,54BSC	
H	14.70	15.10	15.50
L	2,00	2.30	2,60
L1	1,17	1,27	1,40
L2	-	-	1.75
L3		0,25BSC	
L4		2.00REF	
θ	0°	-	8°
θ 1	5°	7°	9°
θ 2	1°	3°	5°

NOTES:
ALL DIMENSIONS REFER TO JEDEC STANDARD TO-263 AB DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.